

# DATA SHEET

## **BSP152**

N-channel enhancement mode  
vertical D-MOS transistor

Product specification  
File under Discrete Semiconductors, SC13b

April 1995

# N-channel enhancement mode vertical D-MOS transistor

**BSP152**

**FEATURES**

- Direct interface to C-MOS, TTL, etc.
- High-speed switching
- No secondary breakdown.

**DESCRIPTION**

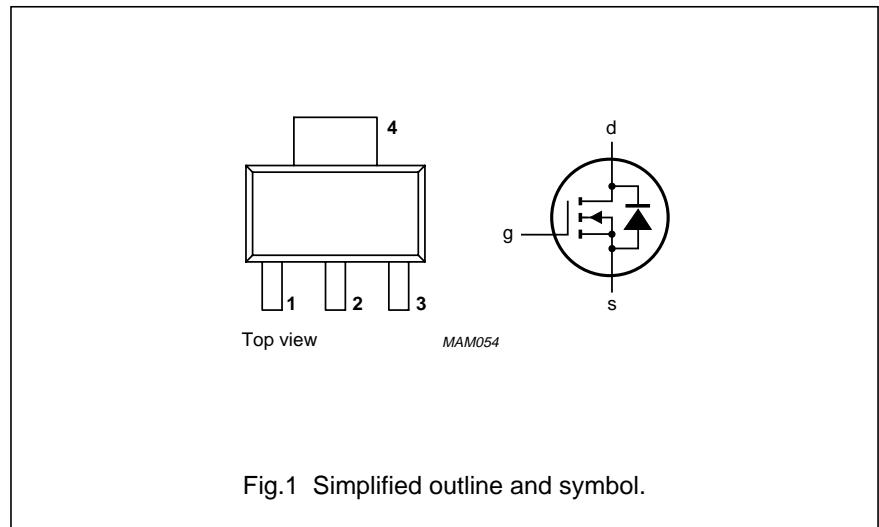
N-channel enhancement mode vertical D-MOS transistor in a SOT223 envelope, intended for use as a line current interruptor in telephone sets and for applications in relay, high-speed and line transformer drivers.

**QUICK REFERENCE DATA**

| SYMBOL        | PARAMETER                   | CONDITIONS                                       | MIN. | MAX. | UNIT     |
|---------------|-----------------------------|--|------|------|----------|
| $V_{DS}$      | drain-source voltage        |  | –    | 200  | V        |
| $I_D$         | DC drain current            |  | –    | 550  | mA       |
| $P_{tot}$     | total power dissipation     | up to $T_{amb} = 25\text{ }^\circ\text{C}$       | –    | 1.5  | W        |
| $\pm V_{GS0}$ | gate-source voltage         | open drain                                       | –    | 40   | V        |
| $R_{DS(on)}$  | drain-source on-resistance  | $I_D = 750\text{ mA};$<br>$V_{GS} = 10\text{ V}$ | –    | 2.5  | $\Omega$ |
| $V_{GS(off)}$ | gate-source cut-off voltage | $I_D = 1\text{ mA};$<br>$V_{DS} = V_{GS}$        | 1.5  | 3.5  | V        |

**PINNING - SOT223**

| PIN | DESCRIPTION |
|-----|-------------|
| 1   | gate        |
| 2   | drain       |
| 3   | source      |
| 4   | drain       |



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## LIMITING VALUES

In accordance with the Absolute Maximum Rating System (IEC 134).

| SYMBOL        | PARAMETER                      | CONDITIONS  | MIN. | MAX. | UNIT             |
|---------------|--------------------------------|---|------|------|------------------|
| $V_{DS}$      | drain-source voltage           |   | –    | 200  | V                |
| $\pm V_{GSO}$ | gate-source voltage            | open drain  | –    | 40   | V                |
| $I_D$         | DC drain current               |   | –    | 550  | mA               |
| $I_{DM}$      | peak drain current             |   | –    | 3    | A                |
| $P_{tot}$     | total power dissipation        | up to $T_{amb} = 25\text{ }^\circ\text{C}$ ; note 1 | –    | 1.5  | W                |
| $T_{stg}$     | storage temperature            |   | –65  | +150 | $^\circ\text{C}$ |
| $T_j$         | operating junction temperature |   | –    | 150  | $^\circ\text{C}$ |

## THERMAL RESISTANCE

| SYMBOL        | PARAMETER                        | THERMAL RESISTANCE |
|---------------|----------------------------------|--------------------|
| $R_{th\ j-a}$ | from junction to ambient; note 1 | 83.3 K/W           |

### Note

- Device mounted on an epoxy printed-circuit board, 40 x 40 x 1.5 mm, mounting pad for the drain tab minimum 6 mm<sup>2</sup>.

## STATIC CHARACTERISTICS

$T_j = 25\text{ }^\circ\text{C}$  unless otherwise specified.

| SYMBOL                                    | PARAMETER                      | CONDITIONS   | MIN. | TYP. | MAX. | UNIT     |
|---|--------------------------------|--|------|------|------|----------|
| $V_{(BR)DSS}$                             | drain-source breakdown voltage | $I_D = 10\ \mu\text{A}$ ; $V_{GS} = 0$   | 200  | –    | –    | V        |
| $\pm I_{GSS}$                             | gate-source leakage current    | $\pm V_{GS} = 40\text{ V}$ ; $V_{DS} = 0$  | –    | –    | 100  | nA       |
| $V_{GS(th)}$                              | gate-source threshold voltage  | $I_D = 1\text{ mA}$ ; $V_{DS} = V_{GS}$  | 1.5  | –    | 3.5  | V        |
| $R_{DS(on)}$                              | drain-source on-resistance     | $I_D = 750\text{ mA}$ ; $V_{GS} = 10\text{ V}$   | –    | –    | 2.5  | $\Omega$ |
| $I_{DSS}$                                 | drain-source leakage current   | $V_{DS} = 160\text{ V}$ ; $V_{GS} = 0$   | –    | –    | 100  | nA       |
| $ Y_{fs} $                                | transfer admittance            | $I_D = 750\text{ mA}$ ; $V_{DS} = 25\text{ V}$   | 400  | –    | –    | mS       |
| $C_{iss}$                                 | input capacitance              | $V_{DS} = 25\text{ V}$ ; $V_{GS} = 0$ ;<br>$f = 1\text{ MHz}$                          | –    | 100  | –    | pF       |
| $C_{oss}$                                 | output capacitance             | $V_{DS} = 25\text{ V}$ ; $V_{GS} = 0$ ; $f = 1\text{ MHz}$                             | –    | 42   | –    | pF       |
| $C_{rss}$                                 | feedback capacitance           | $V_{DS} = 25\text{ V}$ ; $V_{GS} = 0$ ; $f = 1\text{ MHz}$                             | –    | 8    | –    | pF       |
| <b>Switching times (see Figs 2 and 3)</b> |                                |  |      |      |      |          |
| $t_{on}$                                  | turn-on time                   | $I_D = 750\text{ mA}$ ; $V_{DD} = 50\text{ V}$ ;<br>$V_{GS} = 0\text{ to }10\text{ V}$ | –    | –    | 15   | ns       |
| $t_{off}$                                 | turn-off time                  | $I_D = 750\text{ mA}$ ; $V_{DD} = 50\text{ V}$ ;<br>$V_{GS} = 10\text{ to }0\text{ V}$ | –    | –    | 30   | ns       |

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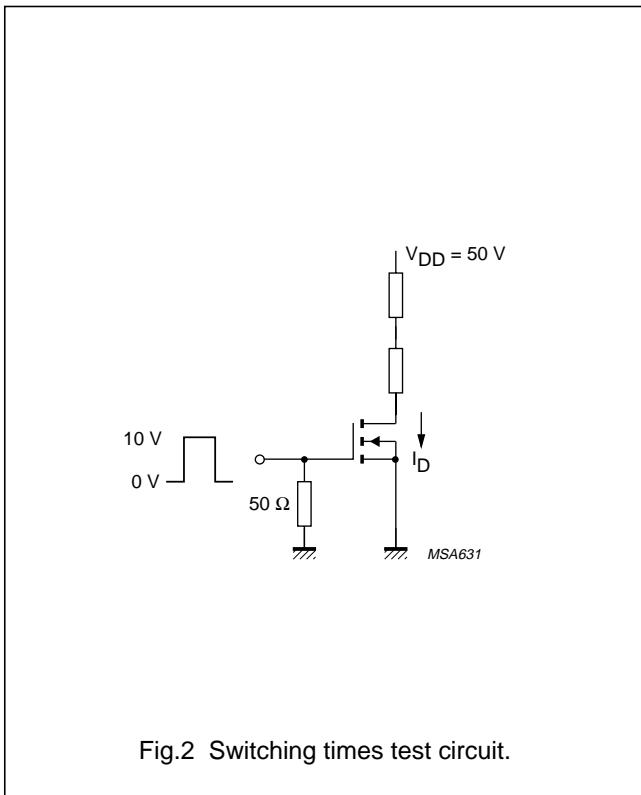


Fig.2 Switching times test circuit.

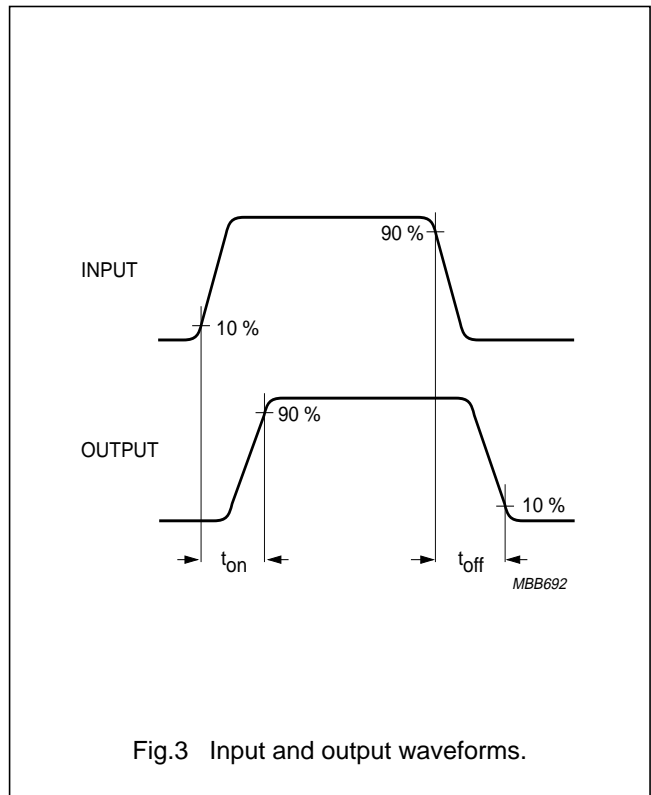


Fig.3 Input and output waveforms.

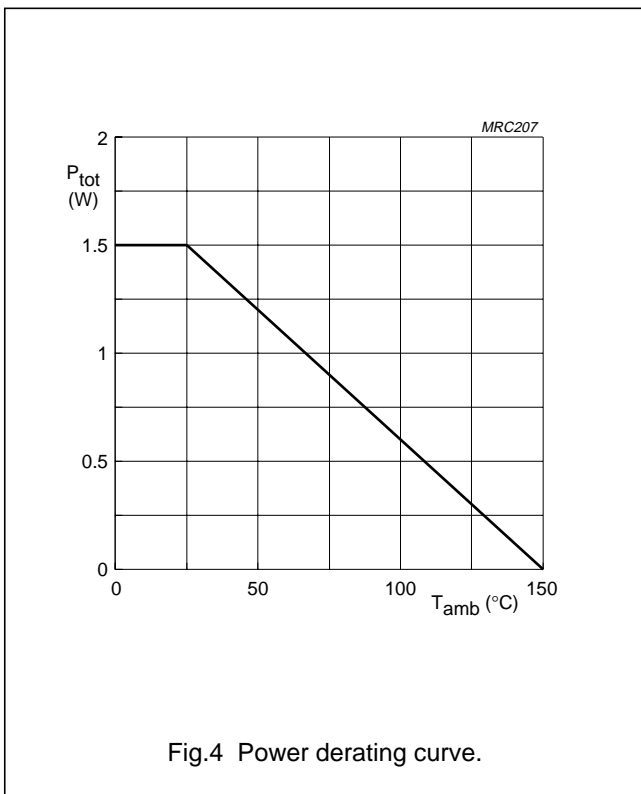
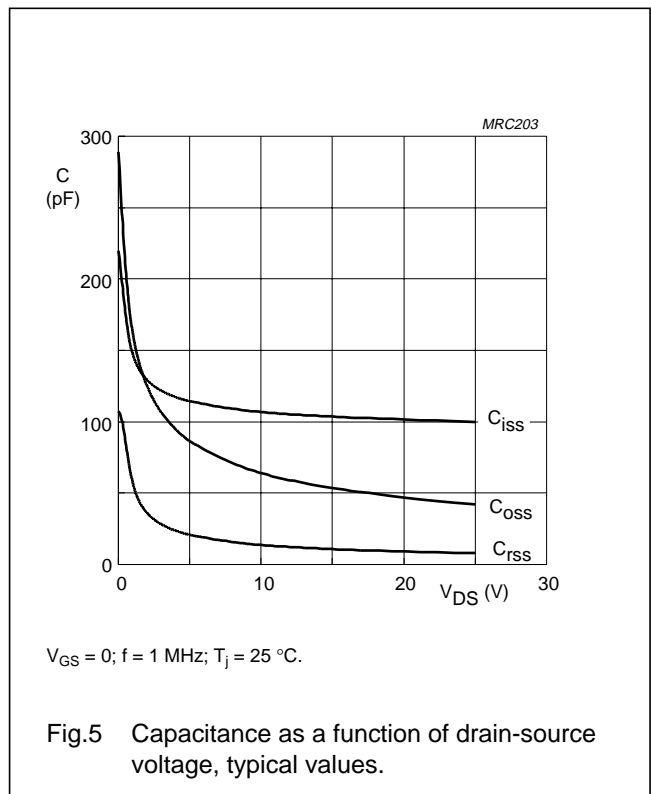


Fig.4 Power derating curve.

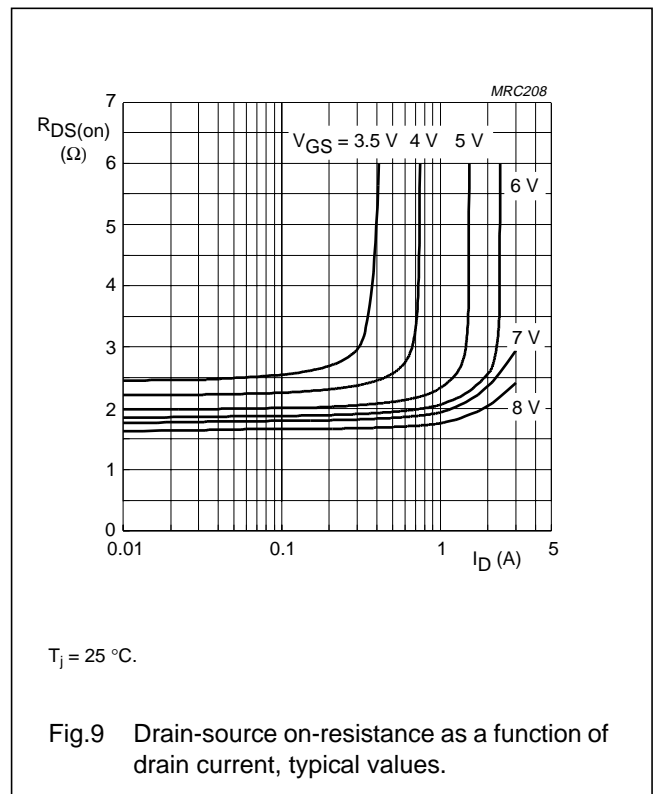
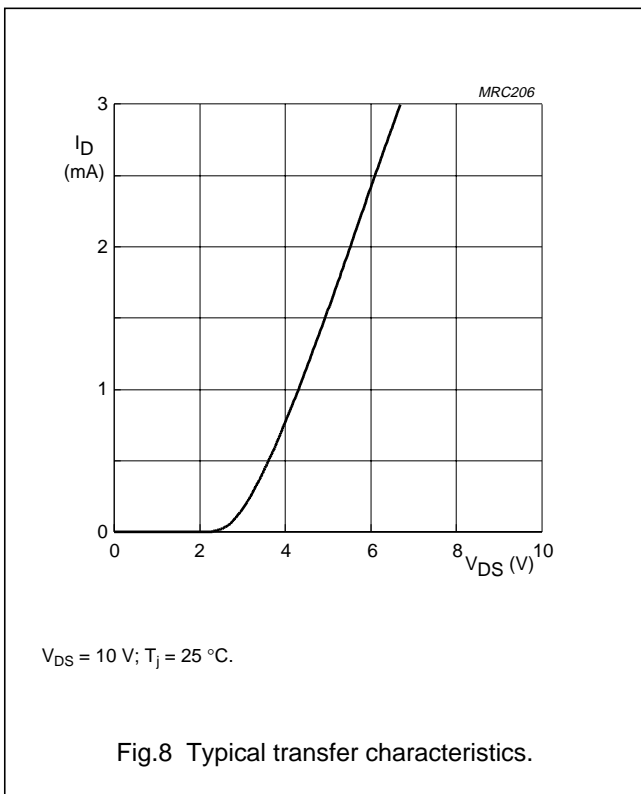
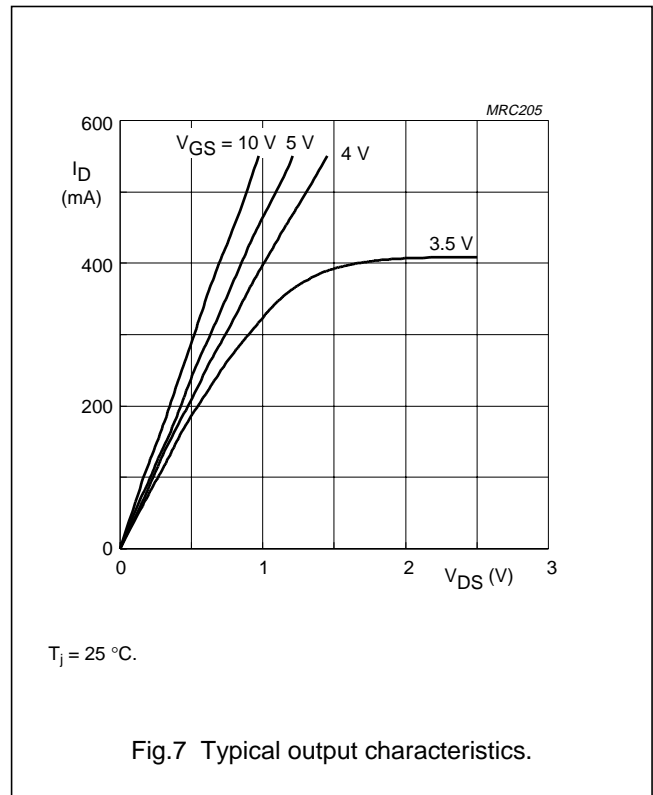
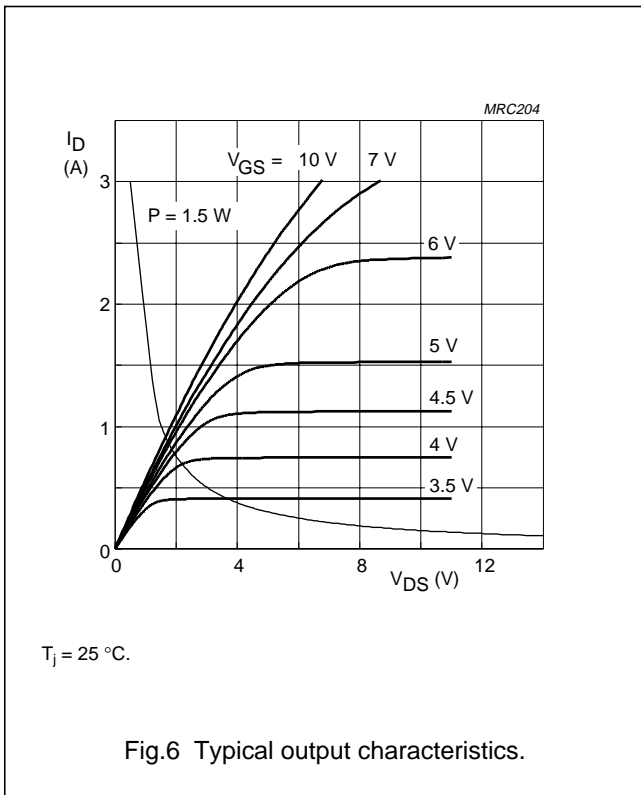


V<sub>GS</sub> = 0; f = 1 MHz; T<sub>j</sub> = 25 °C.

Fig.5 Capacitance as a function of drain-source voltage, typical values.

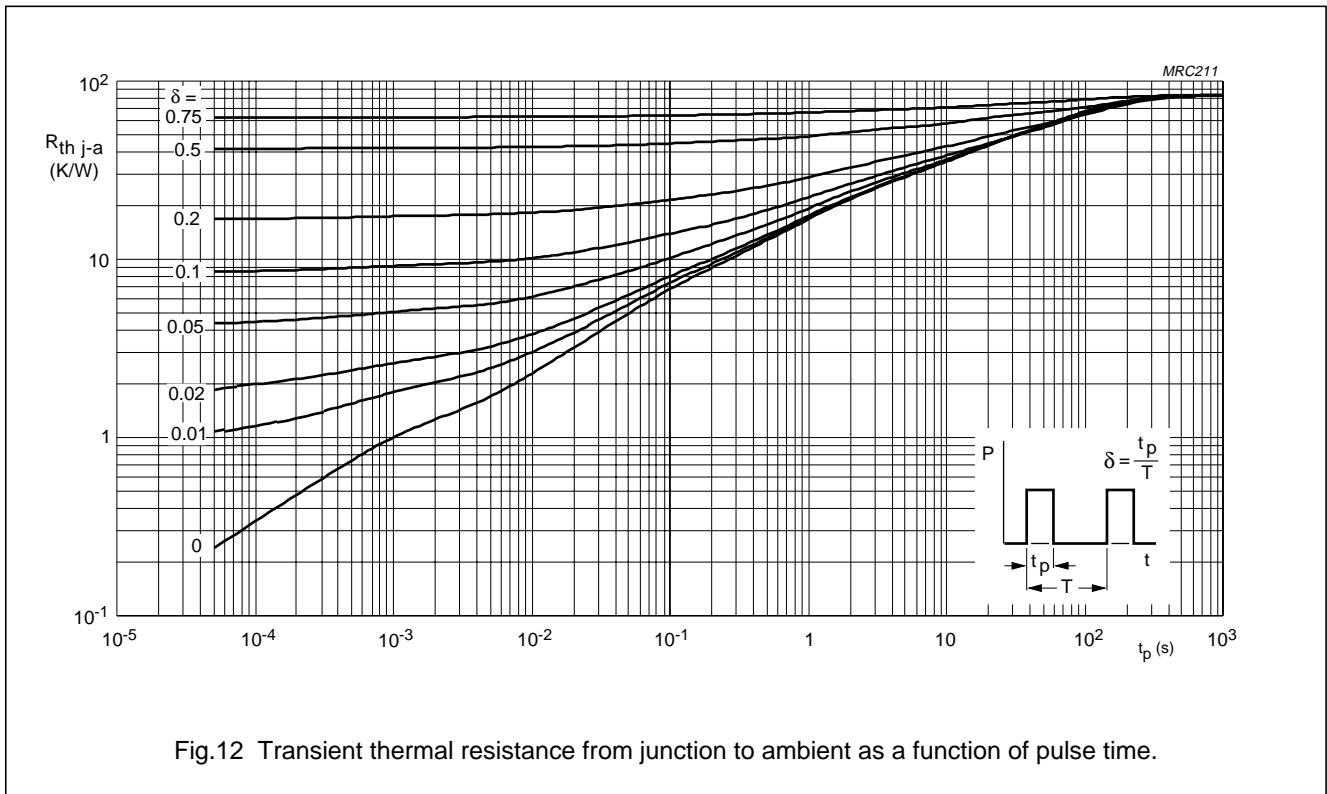
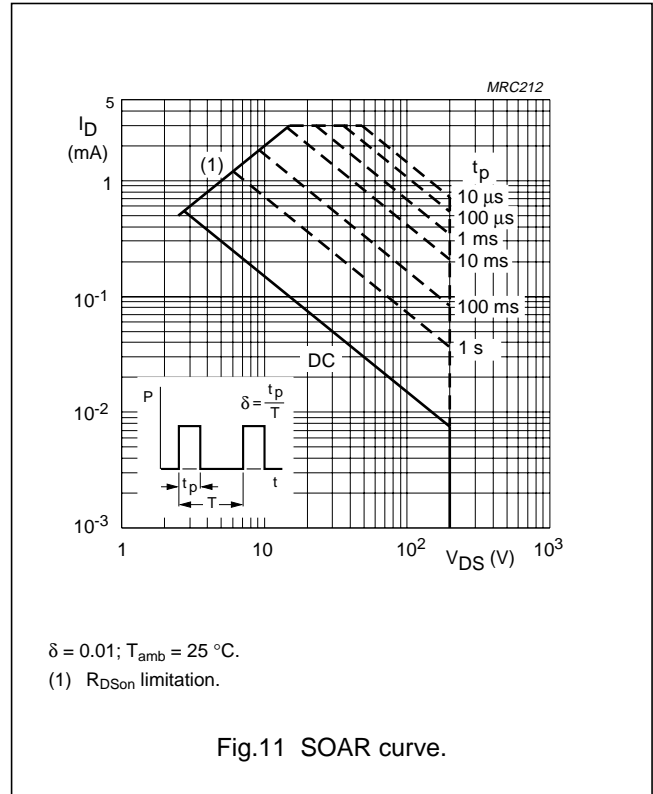
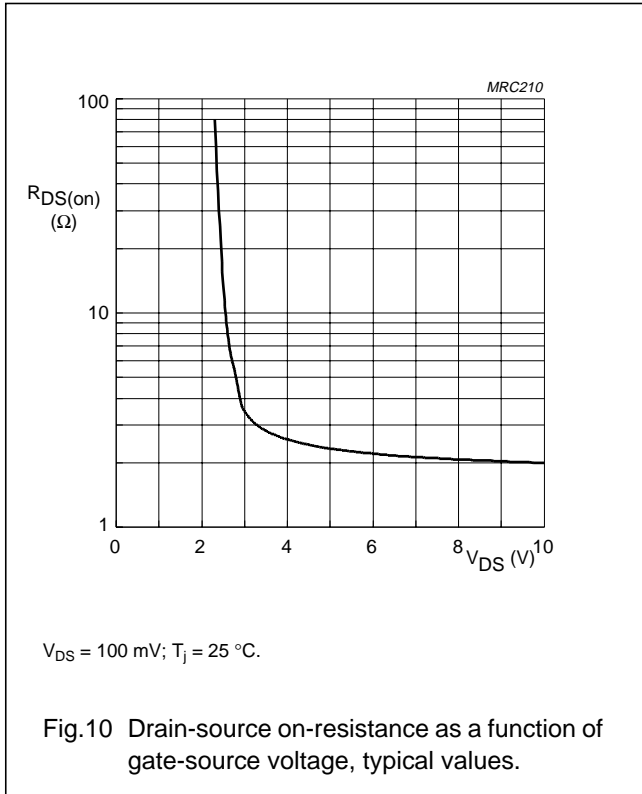
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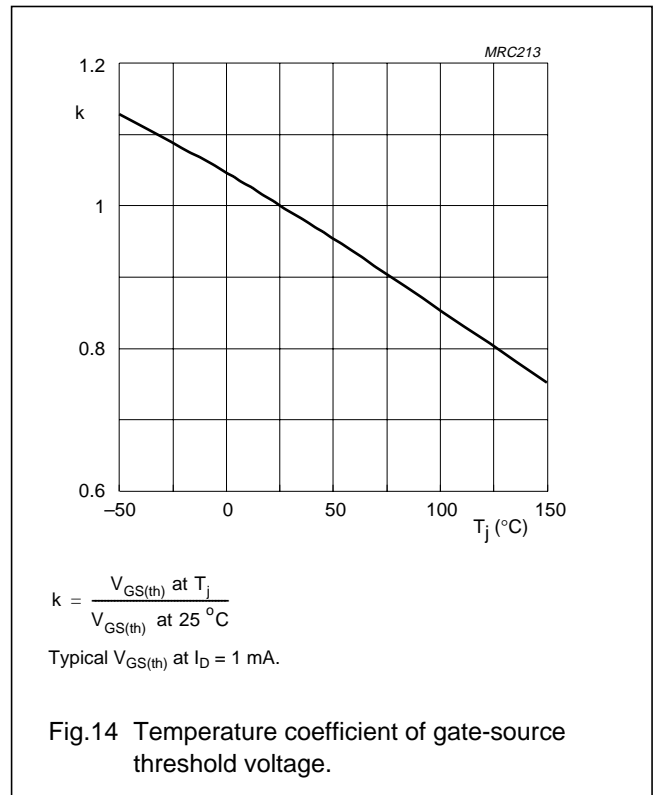
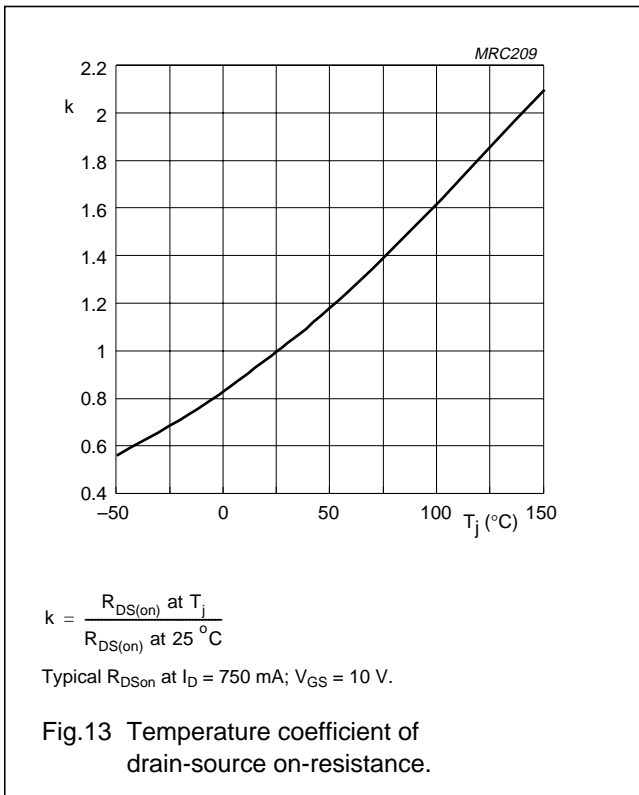
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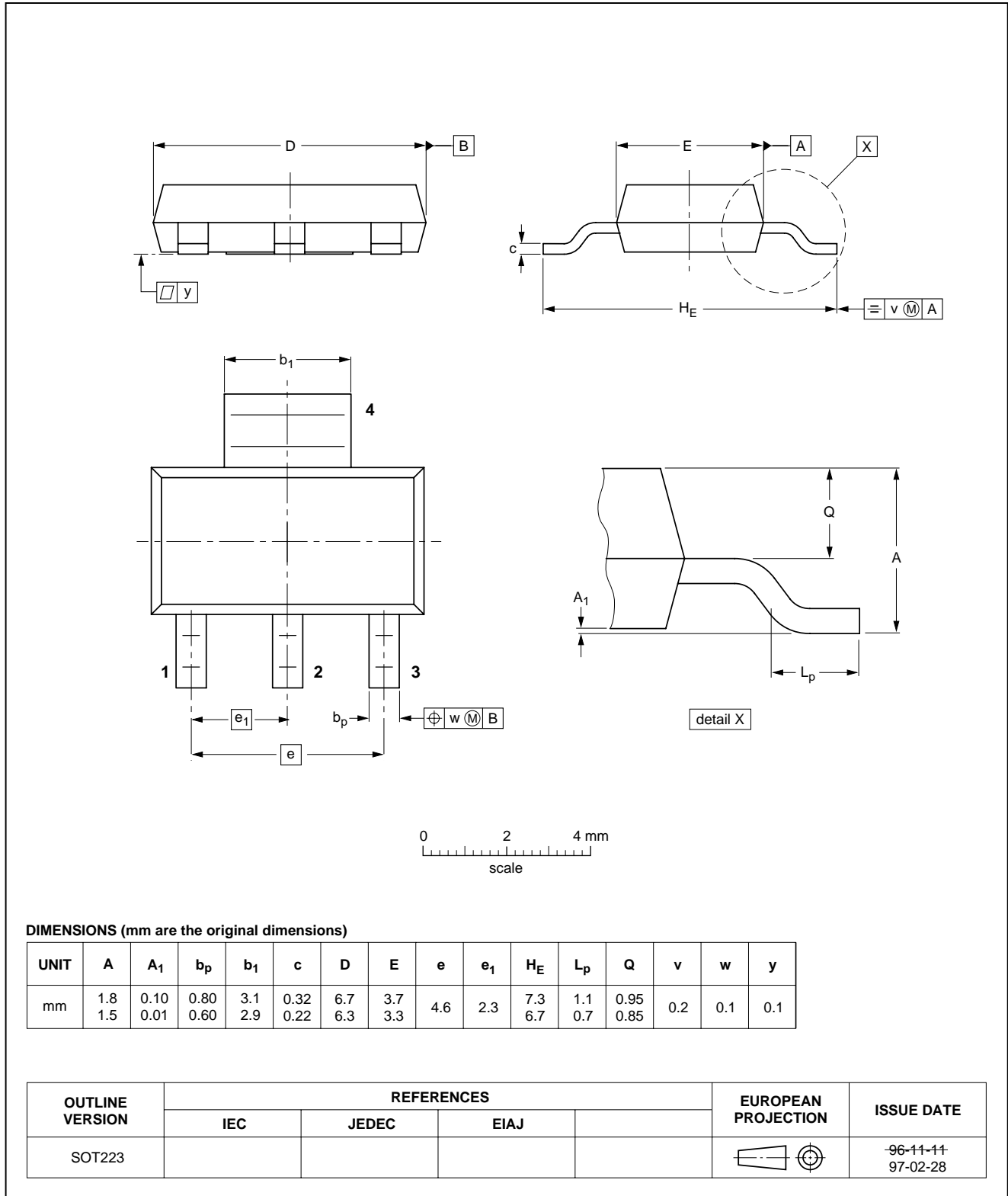
# N-channel enhancement mode vertical D-MOS transistor

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## PACKAGE OUTLINE

Plastic surface mounted package; collector pad for good heat transfer; 4 leads

SOT223



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**BSP152****DEFINITIONS**

| <b>Data sheet status</b>  |   |
|---|---|
| Objective specification   | This data sheet contains target or goal specifications for product development.       |
| Preliminary specification   | This data sheet contains preliminary data; supplementary data may be published later. |
| Product specification   | This data sheet contains final product specifications.                                |
| <b>Application information</b>  |   |
| Where application information is given, it is advisory and does not form part of the specification. |   |

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**NOTES**

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